



AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-8. (Canceled)

9. (Previously presented) An active matrix substrate, comprising:

a pixel electrode provided in a pixel area;

a scanning line and a signal line;

a switching element electrically connected to the scanning line, the signal line, and the pixel electrode;

a storage capacitor electrode for a storage capacitor; and

a storage capacitor common line disposed parallel to the signal line so as to be electrically connected to the storage capacitor electrode, the storage capacitor common line extending across a plurality of pixels, wherein

storage capacitance is provided between the pixel electrode and the storage capacitor electrode,

the scanning line and the storage capacitor electrode are fabricated from a same material in a single patterning; and

wherein the storage capacitor electrode and the storage capacitor common line are patterned in different steps so as to have an insulating film provided partially therebetween.

10. (Original) The active matrix substrate as defined in claim 9, wherein

the signal line and the pixel electrode are fabricated from a single conductive layer through patterning thereof.

11. (Original) The active matrix substrate as defined in claim 9, further comprising an interlayer insulation film on which the pixel electrode is provided.

12. (Previously presented) An active matrix substrate, comprising:
a pixel electrode provided in a pixel area;
a scanning line and a signal line;
a switching element electrically connected to the scanning line, the signal line, and the pixel electrode;
a storage capacitor electrode for a storage capacitor; and
a storage capacitor common line disposed at least partially parallel to the signal line so as to be electrically connected to the storage capacitor electrode, the storage capacitor common line extending across a plurality of pixels, wherein
storage capacitance is provided between the pixel electrode and the storage capacitor electrode,
the scanning line and the storage capacitor electrode are fabricated from a same material in a single patterning; and
wherein in another patterning the signal line, the pixel electrode, and the storage capacitor common line are fabricated of a same material in a single patterning.

13. (Original) The active matrix substrate as defined in claim 9, further comprising a gate insulation film for covering a gate electrode of the switching element, wherein the pixel electrode is disposed opposing the storage capacitor electrode across the gate insulation film.

14. (Currently amended) An active matrix substrate, comprising:
a pixel electrode provided in a pixel area;
a scanning line and a signal line;
a switching element electrically connected to the scanning line, the signal line, and the pixel electrode;
a storage capacitor electrode for a storage capacitor; and
a storage capacitor common line disposed at least partially parallel to the signal line so as to be electrically connected to the storage capacitor electrode, the storage capacitor common line extending across a plurality of pixels, and wherein the signal line and the storage capacitor common line are fabricated of a same material in a single patterning, wherein storage capacitance is provided between the pixel electrode and the storage capacitor electrode,
the scanning line and the storage capacitor electrode are fabricated from a same material in a single patterning;
a protection film for covering the switching element; and
an interlayer insulation film interposed between the pixel electrode and the protection film.

15. (Original) The active matrix substrate as defined in claim 14, wherein
a contact hole is formed through the interlayer insulation film and the protection film so
as to electrically connecting the pixel electrode to the switching element.

16-27. (Canceled)

28. (Original) The active matrix substrate as defined in claim 9, wherein
the scanning line is anodized.

29-34. (Canceled)

35. (Previously presented) An image sensor, comprising:
an active matrix substrate;
a conversion section for converting incident magnetoelectric radiation to electric charges;
and
bias voltage application means for causing a storage capacitor to store the electric
charges, wherein

the active matrix substrate includes:
a pixel electrode provided in a pixel area;
a scanning line and a signal line;
a switching element electrically connected to the scanning line, the signal line, and the
pixel electrode;
a storage capacitor electrode for a storage capacitor; and

a storage capacitor common line disposed at least partially parallel to the signal line so as to be electrically connected to the storage capacitor electrode, the storage capacitor common line extending across a plurality of pixels, wherein

the scanning line and the storage capacitor electrode are fabricated from a same material in a single patterning; and

wherein the storage capacitor electrode and the storage capacitor common line are patterned in different steps so as to have an insulating film provided partially therebetween.

36. (Original) The image sensor as defined in claim 35, further comprising:
a gate insulation film for covering a gate electrode of the switching element; and
a conductive body layer deposited on the gate insulation film so as to be connected to the switching element, wherein

the storage capacitor electrode and the conductive body layer constitute the storage capacitor across the gate insulation film.

37. (Original) The image sensor as defined in claim 35, wherein the scanning line is anodized.

38-41. (Canceled)

42. (Currently amended) An active matrix substrate, comprising:
a pixel electrode provided in each pixel area bounded by a scanning line and a signal line that are disposed in a matrix as a whole;

a switching element connected to the scanning line, the signal line, and the pixel electrode;

a storage capacitor electrode for constituting a storage capacitor; and

a storage capacitor common line disposed parallel to the signal line so as to be connected to the storage capacitor electrode, the storage capacitor common line extending across a plurality of pixels, wherein

the storage capacitor is formed between the pixel electrode and the storage capacitor electrode,

the scanning line and the storage capacitor electrode are fabricated from a single electrode layer through patterning thereof, and

the signal line and the storage capacitor common line ~~pixel electrode~~ are fabricated ~~from~~ of a same material in a single conductive layer through patterning thereof.